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Product Data Sheet

UV LED Chip

EOLC-365-34

Rev. 03, 2017

Radiation	Type	Electrodes
Ultraviolet	GaN / sapphire	P + N up

	<p>Description</p> <ul style="list-style-type: none"> - Substrate: Sapphire, epitaxial layer: GaN based material - N bonding pad electrode: Au alloy - P bonding pad electrode: Au alloy - Emission area: 201 μm x 201 μm - Bottom area: 280 μm x 280 μm ± 20 μm - Chip thickness: 120 ± 10 μm - Bonding pad electrodes: (each) 90 μm - Electrodes spacing: 128 μm
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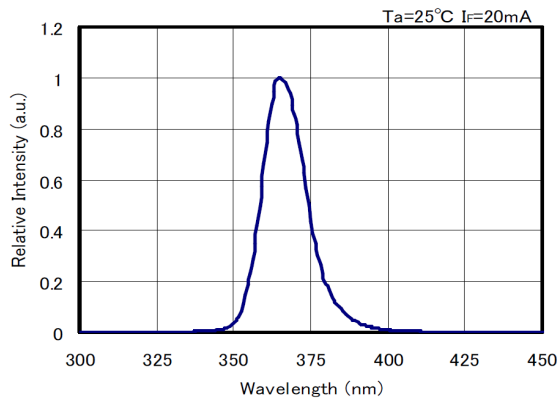
Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20 mA	V _F	3.2	3.6	4.2	V
Reverse current	V _R =5 V	I _R			10	μA
Peak wavelength	I _F =20 mA	λ _p	363		370	nm
FWHM	I _F =20 mA	Δλ _{0.5}		15		nm
Radiant power	I _F =20 mA	Φ _e	1.0		1.5	mW

*Measured on bare chip on TO-18 header

Spectrum



Art. No. 111 002



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.